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(54) **METHOD AND CIRCUIT FOR COLLECTING
MEMORY FAILURE INFORMATION**

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(*) Notice: Subject to any disclaimer, the term of this
patent is extended or adjusted under 35
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(58) **Field of Classification Search** **714/723**
See application file for complete search history.

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(57) **ABSTRACT**

A method and circuit for collecting memory failure infor-
mation on-chip and unloading the information in real time
while performing a test of memory embedded in a circuit
comprises, for each column or row of a memory under test,
testing each memory location of the column or row accord-
ing to a memory test algorithm under control of a first clock,
selectively generating a failure summary on-circuit while
testing each column or row of the memory; and transferring
the failure summary from the circuit under control of a
second clock within the time required to test the next column
or row, if any, of the memory under test.

54 Claims, 15 Drawing Sheets

